2SK3233

Silicon N Channel MOS FET
High Speed Power Switching

HITACHI

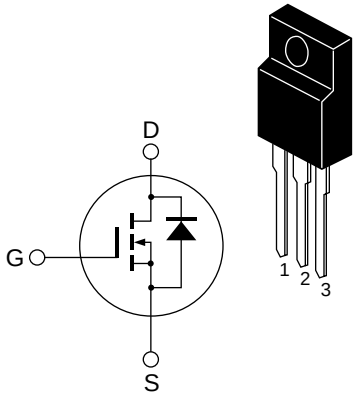
ADE-208-1369 (Z)
1st. Edition
Mar. 2001

Features

- Low on-resistance: $R_{DS(on)}$ = 1.1 Ω typ.
- Low leakage current: IDSS = 1 µA max (at VDS = 500 V)
- High speed switching: tf = 15 ns typ (at VGS = 10 V, VDD = 250 V, ID = 2.5 A)
- Low gate charge: Qg = 15 nC typ (at VDD = 400 V, VGS = 10 V, ID = 5 A)
- Avalanche ratings

Outline

TO–220CFM



1. Gate
2. Drain
3. Source

Hitachi semiconductor

Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings	Unit
Drain to source voltage	V_{DSS}	500	V
Gate to source voltage	V_{GSS}	±30	V
Drain current	I_D	5	A
Drain peak current	$I_{D\ (pulse)}$ Note1	20	A
Body-drain diode reverse drain current	I_{DR}	5	A
Body-drain diode reverse drain peak current	$I_{DR\ (pulse)}$ Note1	20	A
Avalanche current	I_{AP} Note3	5	A
Channel dissipation	Pch Note2	30	W
Channel to case Tehrmal Impedance	θ ch-c	4.17	°C/W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	–55 to +150	°C

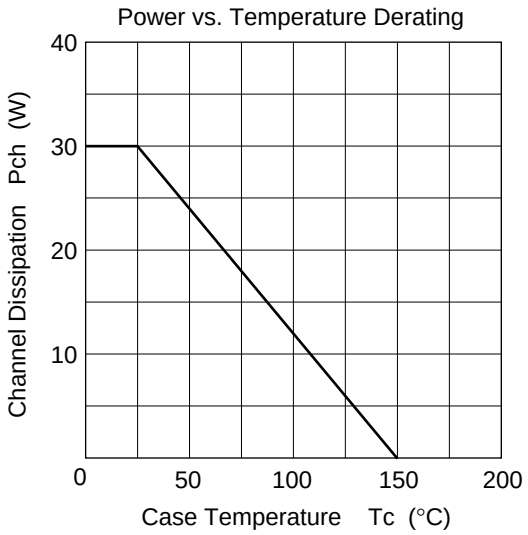
Notes: 1. PW ≤ 10 µs, duty cycle ≤ 1%
2. Value at Tc = 25°C
3. Tch ≤ 150°C

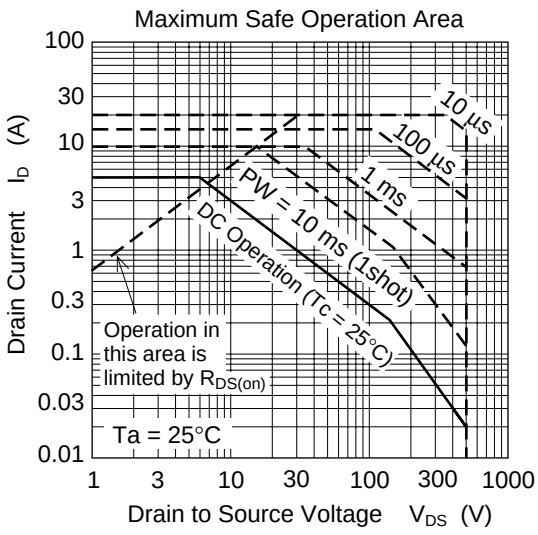
Electrical Characteristics (Ta = 25°C)

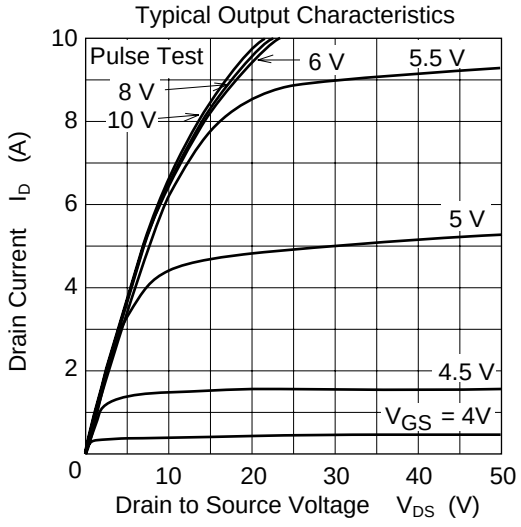
Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	500	—	—	V	I_D = 10 mA, V_{GS} = 0
Gate to source leak current	I_{GSS}	—	—	±0.1	µA	V_{GS} = ±30 V, V_{DS} = 0
Zero gate voltage drain current	I_{DSS}	—	—	1	µA	V_{DS} = 500 V, V_{GS} = 0
Gate to source cutoff voltage	$V_{GS(off)}$	3.0	—	4.0	V	V_{DS} = 10 V, I_D = 1 mA
Static drain to source on state resistance	$R_{DS(on)}$	—	1.1	1.5	Ω	I_D = 2.5 A, V_{GS} = 10 V [Note4]
Forward transfer admittance	$\|y_{fs}\|$	3.0	4.5	—	S	I_D = 2.5 A, V_{DS} = 10 V [Note4]
Input capacitance	Ciss	—	580	—	pF	V_{DS} = 25 V
Output capacitance	Coss	—	70	—	pF	V_{GS} = 0
Reverse transfer capacitance	Crss	—	13	—	pF	f = 1 MHz
Turn-on delay time	td(on)	—	20	—	ns	I_D = 2.5 A
Rise time	tr	—	15	—	ns	V_{GS} = 10 V
Turn-off delay time	td(off)	—	65	—	ns	R_L = 100 Ω
Fall time	tf	—	15	—	ns	Rg = 10 Ω
Total gate charge	Qg	—	15	—	nC	V_{DD} = 400 V
Gate to source charge	Qgs	—	3	—	nC	V_{GS} = 10 V
Gate to drain charge	Qgd	—	8	—	nC	I_D = 5 A
Body-drain diode forward voltage	V_{DF}	—	0.85	1.3	V	I_F = 5 A, V_{GS} = 0
Body-drain diode reverse recovery time	trr	—	400	—	ns	I_F = 5 A, V_{GS} = 0
Body-drain diode reverse recovery charge	Qrr	—	1.5	—	µC	diF/dt = 100 A/µs

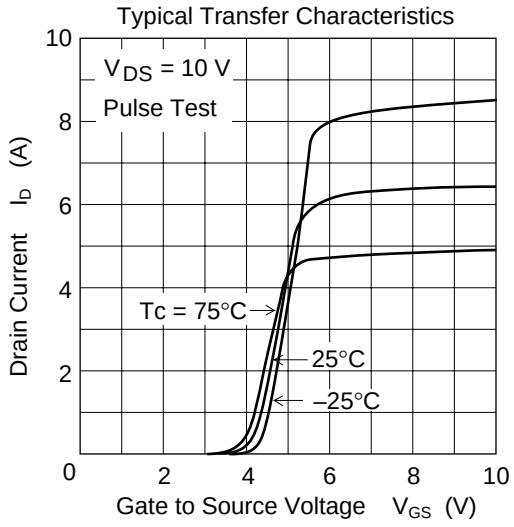
Note: 4. Pulse test

Main Characteristics

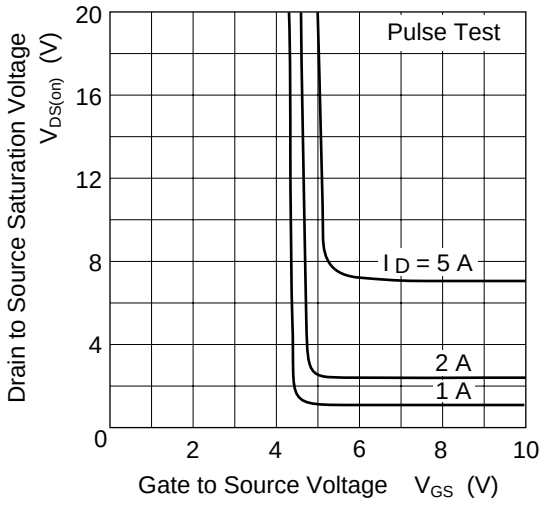




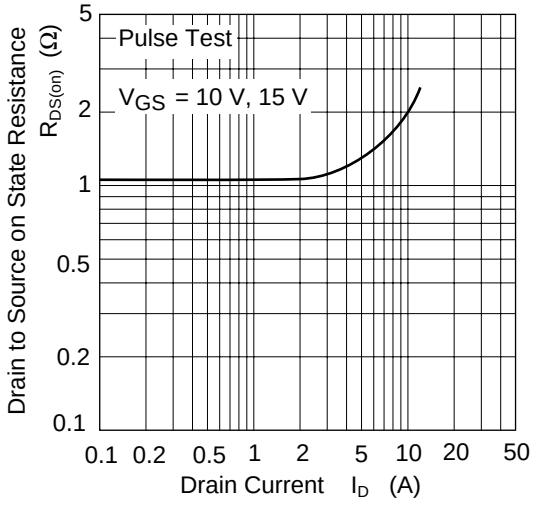




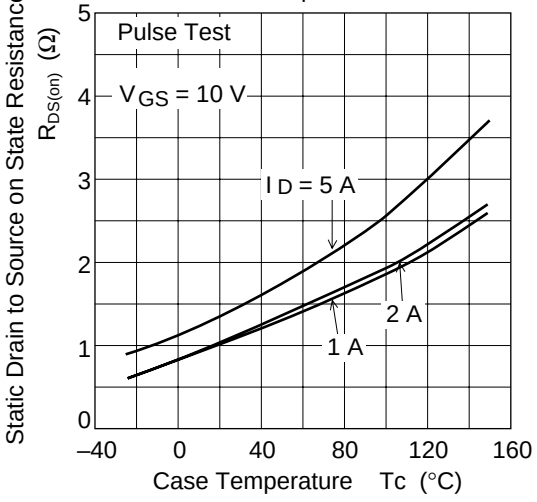
Drain to Source Saturation Voltage vs. Gate to Source Voltage



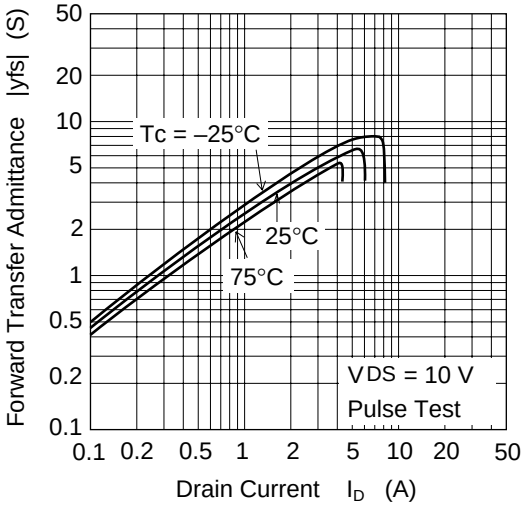
Static Drain to Source on State Resistance vs. Drain Current



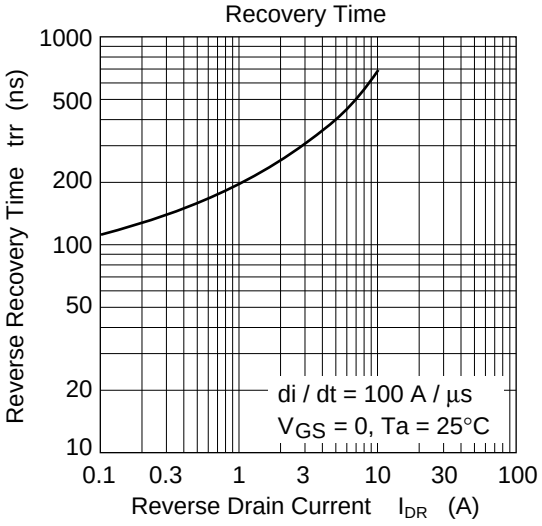
Static Drain to Source on State Resistance vs. Temperature



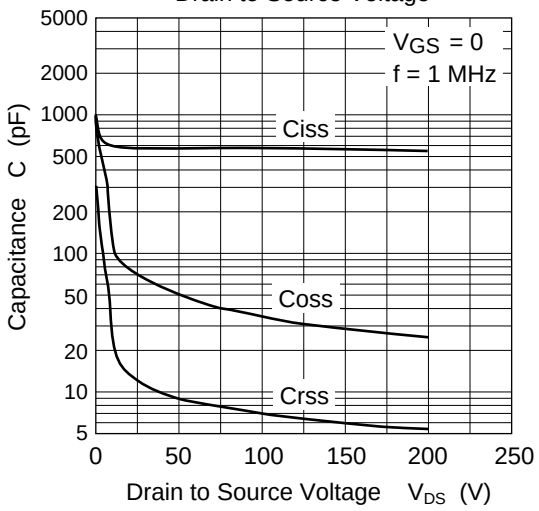
Forward Transfer Admittance vs. Drain Current



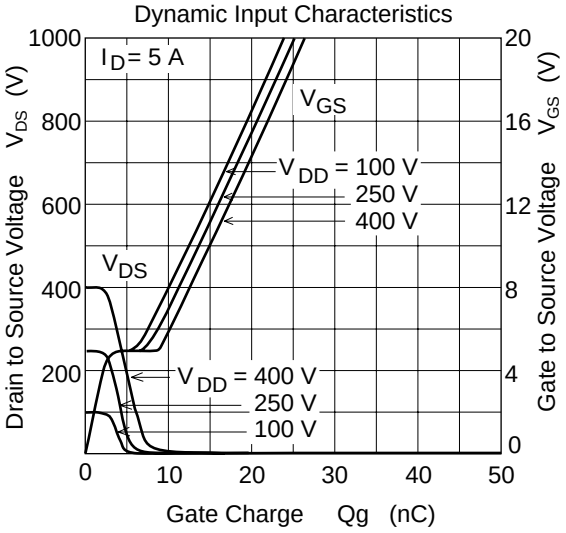
Body-Drain Diode Reverse Recovery Time



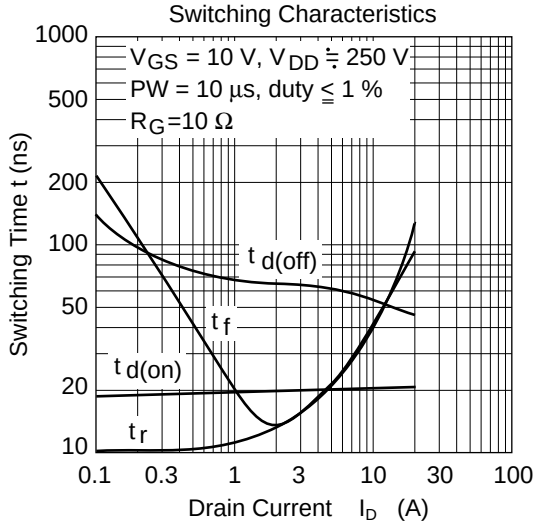
Typical Capacitance vs. Drain to Source Voltage



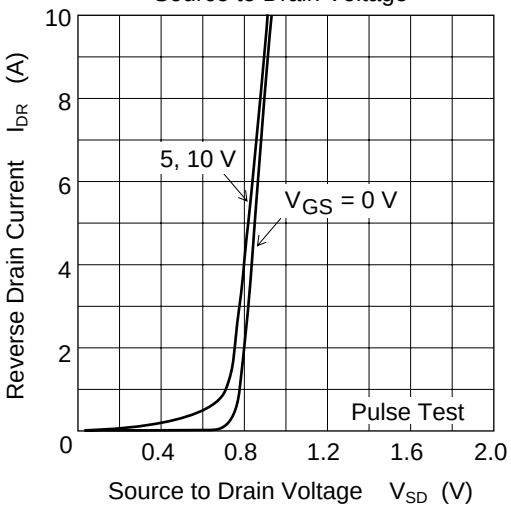
Dynamic Input Characteristics



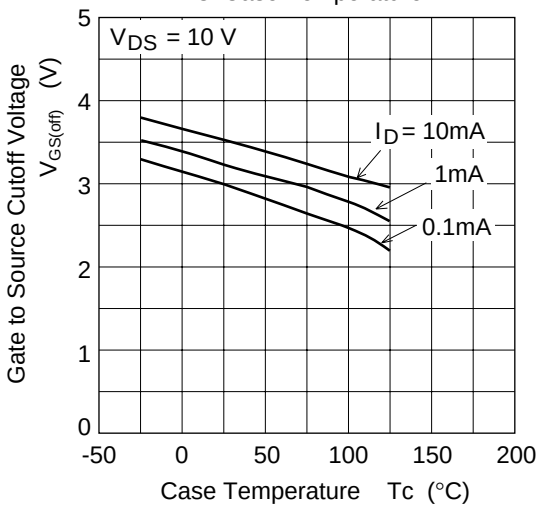
Switching Characteristics



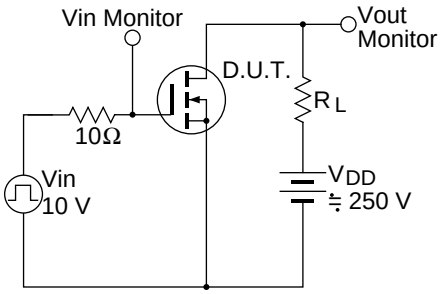
Reverse Drain Current vs. Source to Drain Voltage



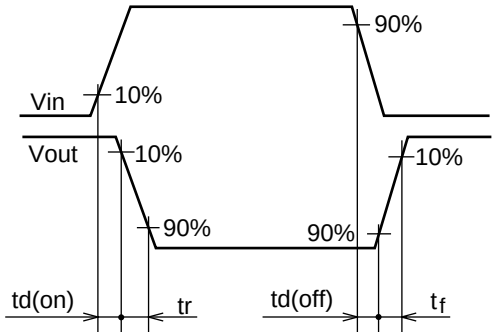
Gate to Source Cutoff Voltage vs. Case Temperature

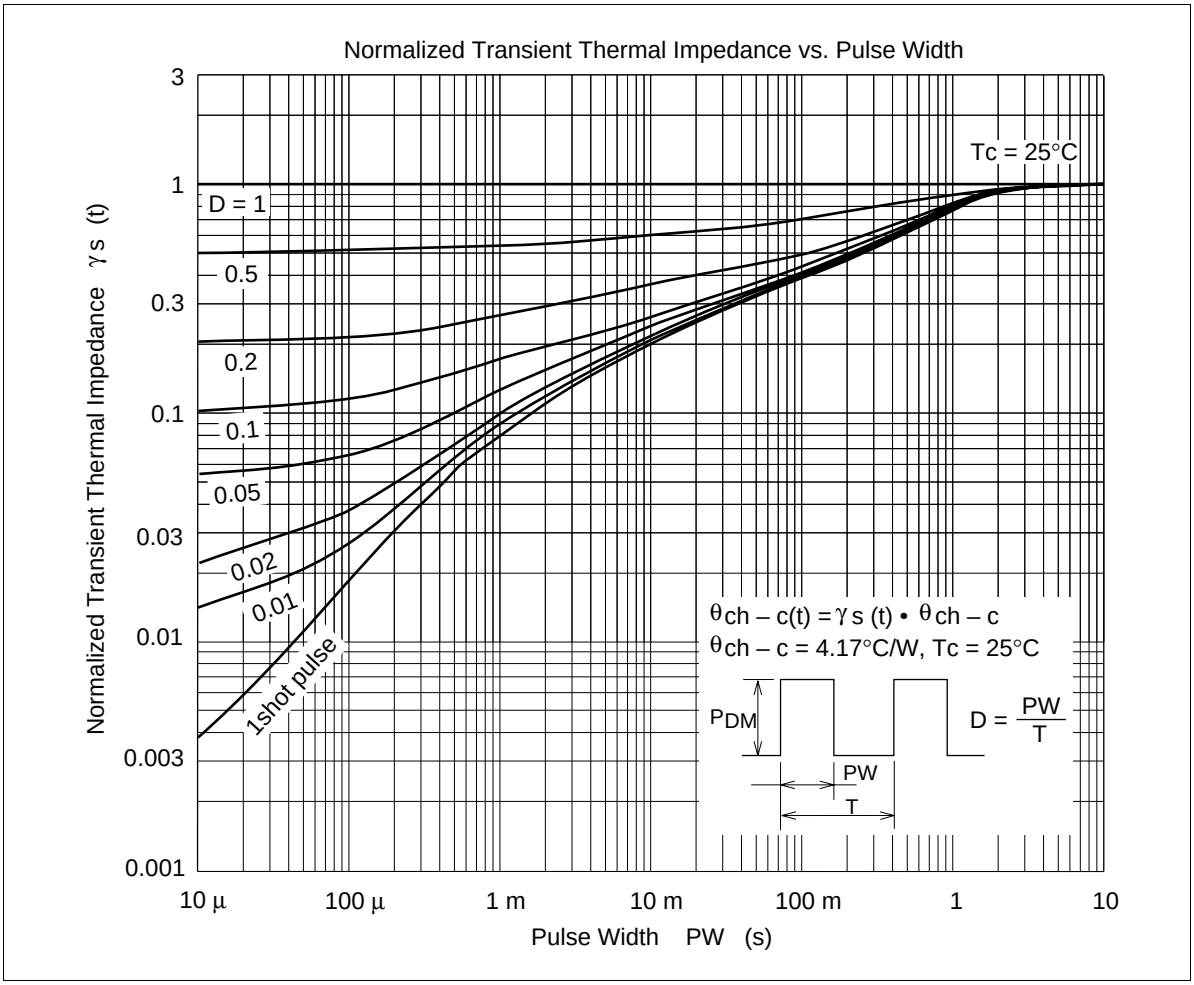


Switching Time Test Circuit



Waveform

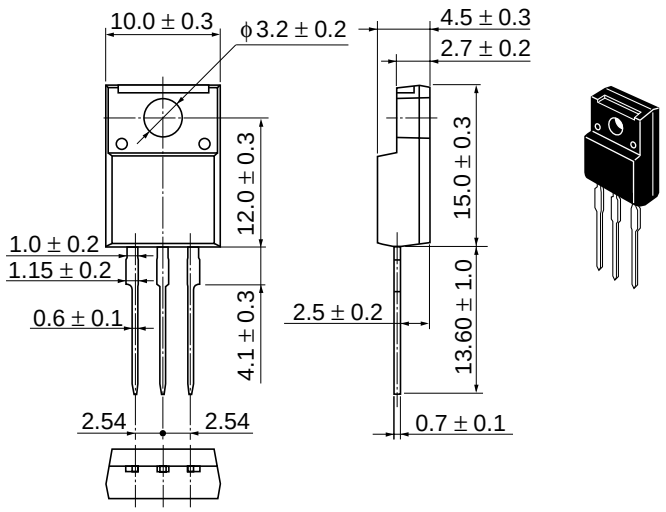




Package Dimensions

As of January, 2001

Unit: mm



Hitachi Code	TO-220CFM
JEDEC	—
EIAJ	—
Mass (reference value)	1.9 g

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